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[54] **METHOD OF AND APPARATUS FOR PROCESSING PHOTORESIST, METHOD OF EVALUATING PHOTORESIST FILM, AND PROCESSING APPARATUS USING THE EVALUATION METHOD**

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[52] **U.S. Cl.** **396/604**; 396/611; 118/52

[58] **Field of Search** 396/604, 611, 396/627; 118/52, 666, 712, 665; 427/335, 385.5

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[57] **ABSTRACT**

A resist processing method includes setting a substrate at a specific temperature, forming a resist film on the substrate by applying a resist solution onto the substrate while turning the substrate set at the specific temperature, heating the substrate on which the resist film has been formed, cooling the substrate a specific temperature after the heating process, wherein the thickness of the resist film on the substrate is measured between the heating process and the cooling process.

22 Claims, 14 Drawing Sheets